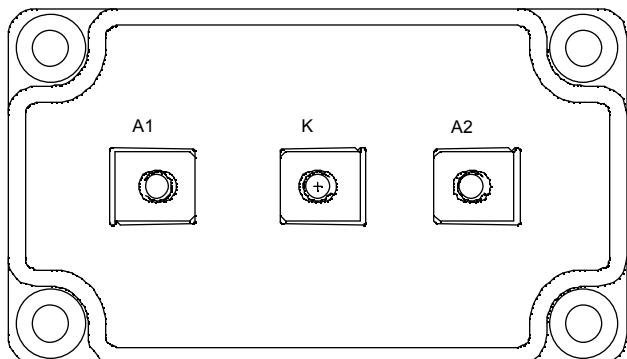
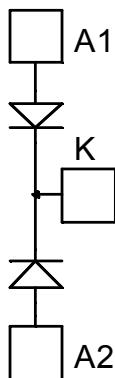




**Dual Common Cathode diodes  
Power Module**

**V<sub>RRM</sub> = 200V  
I<sub>C</sub> = 400A @ T<sub>c</sub> = 80°C**



**Absolute maximum ratings**

Symbol	Parameter	Max ratings		Unit
V <sub>R</sub>	Maximum DC reverse Voltage	200		V
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage	T <sub>C</sub> = 25°C	500	A
I <sub>F(AV)</sub>	Maximum Average Forward Current		400	
I <sub>F(RMS)</sub>	RMS Forward Current	T <sub>C</sub> = 45°C	500	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	8.3ms	T <sub>C</sub> = 45°C	3000

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

### Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_F$	Diode Forward Voltage	$I_F = 400\text{A}$		1.0	1.1		V
		$I_F = 800\text{A}$		1.4			
		$I_F = 400\text{A}$	$T_j = 125^\circ\text{C}$	0.9			
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$			750	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			1000	
$C_T$	Junction Capacitance	$V_R = 200\text{V}$			1600		pF

### Dynamic Characteristics

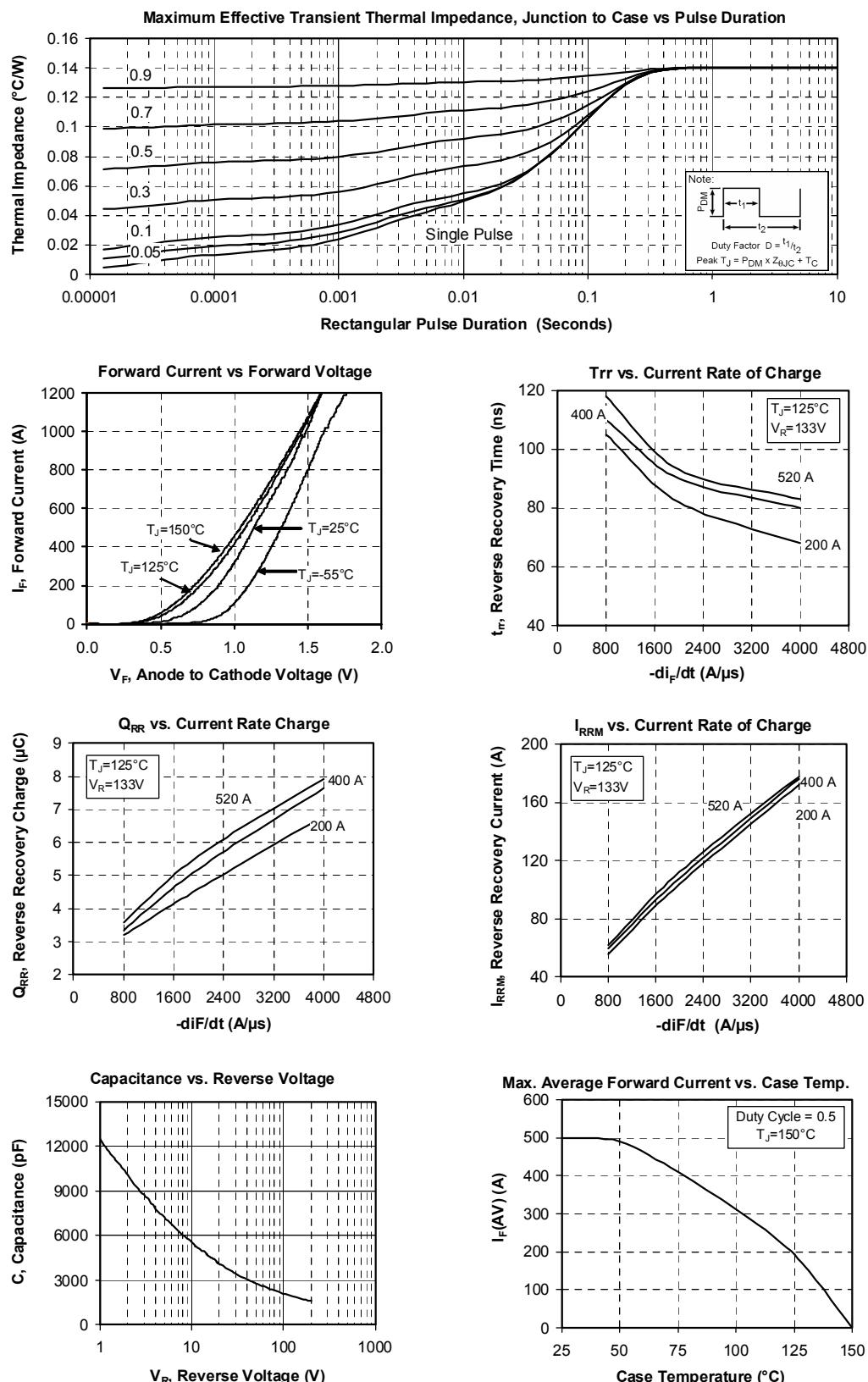
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$t_{rr}$	Reverse Recovery Time	$I_F=1\text{A}, V_R=30\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		39		ns
$t_{rr}$	Reverse Recovery Time		$T_j = 25^\circ\text{C}$		60		ns
			$T_j = 125^\circ\text{C}$		110		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 400\text{A}$ $V_R = 133\text{V}$ $di/dt = 800\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		800		nC
			$T_j = 125^\circ\text{C}$		3360		
$I_{RRM}$	Reverse Recovery Current		$T_j = 25^\circ\text{C}$		24		A
			$T_j = 125^\circ\text{C}$		60		
$t_{rr}$	Reverse Recovery Time	$I_F = 400\text{A}$ $V_R = 133\text{V}$ $di/dt = 4000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		80		ns
$Q_{rr}$	Reverse Recovery Charge				7.64		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current				176		A

### Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance			0.14	$^\circ\text{C}/\text{W}$
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, $I_{isol} < 1\text{mA}$ , 50/60Hz	2500			V
$T_j$	Operating junction temperature range	-40		150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-40		125	
$T_c$	Operating Case Temperature	-40		100	
Torque	Mounting torque	To heatsink	M6	3	5
		For terminals	M5	2	3.5
Wt	Package Weight			280	g

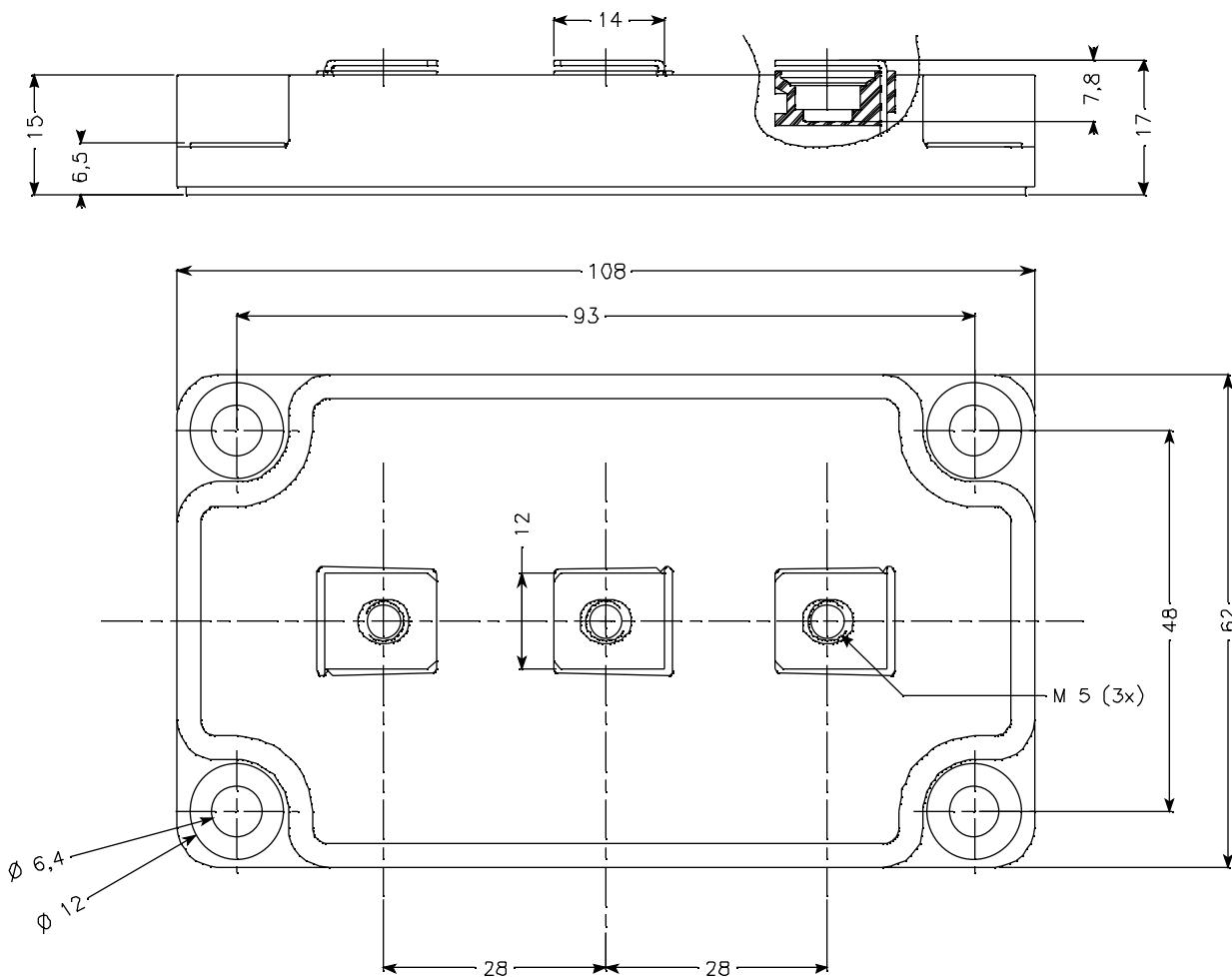


## Typical Performance Curve





**SP6 Package outline (dimensions in mm)**



**Microsemi reserves the right to change, without notice, the specifications and information contained herein**

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.